

AMENDMENTS TO THE CLAIMS

1. (Currently Amended): A method for forming a pattern over a substrate, comprising:
 - providing a master having at least one opening;
 - providing a substrate having an etching layer formed thereon;
 - locating the master over the etching layer, the master being separated from the substrate at a distance having at least one opening;
 - filling a resist in the at least one opening of the master; and
 - separating the master from the substrate to leave the resist on the substrate,wherein the master is separated separately formed from the substrate at a distance during filling the resist in opening of the mater so that the master is separable from the substrate.
2. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - contacting a resist supplying roll to the master; and
 - filling the resist in the at least one opening of the master by rotating the resist supplying roll over the at least one opening of the master.
3. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - applying the resist on the master; and
 - planarizing the applied resist on the surface of the master by using a doctor blade.
4. (Original): The method of claim 1, wherein the master is separated apart from the substrate by a few micrometers (μm).
5. (Original): The method of claim 1, wherein the etching layer is a metal layer.
6. (Original): The method of claim 1, wherein the etching layer is an insulating layer.
7. (Original): The method of claim 6, wherein the insulating layer is formed of one

of SiO_x or SiN_x.

8. (Original): The method of claim 1, wherein the etching layer is a semiconductor layer.

9. (Original): The method of claim 1, further comprising hardening the resist.

10. (Currently Amended): A method for forming a pattern over a substrate, comprising:

- providing a master having at least one opening;
- providing a substrate having an etching layer formed thereon;
- placing the master over an area corresponding to the etching layer to be etched, the master being separated from the substrate at a distance;
- applying a resist on the master;
- planarizing the applied resist on the surface of the master and filling the resist in the at least one opening by using a doctor blade;
- hardening the planarized resist; and
- forming a resist pattern on the etching layer by separating the master from the substrate, wherein the master is separated separately formed from the substrate at a distance during filling the resist in opening of the mater so that the master is separable from the substrate.

11. The method of claim 10, wherein the master is separated apart from the substrate by a few micrometers (μm).

12. (Current Amended): A method for forming a pattern over a substrate, comprising:

- providing a master having at least one opening
- providing a substrate having an etching layer formed thereon;
- placing the master over the etching layer, the opening of the master being corresponding to the etching region to be etched;
- contacting a resist supplying roll on the master to fill the resist in the at least one opening of the master, the master being separated from the substrate at a distance;
- hardening the filled resist in the at least one opening of the master; and
- forming a resist pattern on the etching layer by separating mechanically the master from

the substrate,

wherein the master is separated ~~separately formed~~ from the substrate at a distance during filling the resist in opening of the mater ~~so that the master is separable from the substrate~~.

13. The method of claim 12, wherein the master is separated apart from the substrate by a few micrometers (μm).